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May 2010

FDB8832_F085

N-Channel Logic Level PowerTrench® MOSFET 30V, 80A, 2.1m Ω

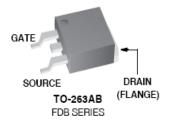
Features

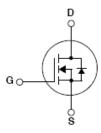
- Typ $r_{DS(on)} = 1.5m\Omega$ at $V_{GS} = 5V$, $I_D = 80A$
- Typ $Q_{g(5)} = 100nC$ at $V_{GS} = 5V$
- Low Miller Charge
- Low Q_{rr} Body Diode
- UIS Capability (Single Pulse and Repetitive Pulse)
- Qualified to AEC Q101
- RoHS Compliant



Applications

- 12V Automotive Load Control
- Starter / Alternator Systems
- Electronic Power Steering Systems
- ABS
- DC-DC Converters





MOSFET Maximum Ratings $T_C = 25$ °C unless otherwise noted

Symbol	Parameter	Ratings	Units	
V_{DSS}	Drain to Source Voltage	30	V	
V_{GS}	Gate to Source Voltage	±20	V	
	Drain Current Continuous (T _C < 165°C, V _{GS} = 10V)	80		
	Drain Current Continuous (T _C < 163°C, V _{GS} = 5V)	80	Α	
'D	Drain Current Continuous (T _{amb} = 25°C, V _{GS} = 10V, with R _{θJA} = 43°C/W)	34	7 ^	
	Pulsed	See Figure 4		
E _{AS}	Single Pulse Avalanche Energy (Note 1)	1246	mJ	
D	Power Dissipation	300	W	
P_D	Derate above 25°C	2	W/°C	
T_J , T_{STG}	Operating and Storage Temperature	-55 to +175	°C	

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case 0.5			
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 2)		62	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, lin ² copper pad area		43	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB8832	FDB8832_F085	TO-263AB	330mm	24mm	800 units

Electrical Characteristics $T_J = 25$ °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Cha	racteristics	·				
B _{VDSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V$	30	-	-	V
1	Zero Gate Voltage Drain Current	V _{DS} = 24V	-	-	1	
I _{DSS} Zero Gate Voltage	Zero Gate Voltage Drain Current	$V_{GS} = 0V$ $T_J = 150^{\circ}C$	-	-	250	μΑ
I _{GSS}	Gate to Source Leakage Current	V _{GS} = ±20V	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0	1.6	3.0	V
	r _{DS(on)} Drain to Source On Resistance	$I_D = 80A, V_{GS} = 10V$	-	1.4	1.9	
		$I_D = 80A, V_{GS} = 5V$	-	1.5	2.1	
r _{DS(on)}		$I_D = 80A, V_{GS} = 4.5V$	-	1.6	2.2	mΩ
		I _D = 80A, V _{GS} = 10V T _J = 175°C	-	2.3	3.0	

Dynamic Characteristics

C _{iss}	Input Capacitance	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz		=	11400	-	pF
C _{oss}	Output Capacitance			-	2140	ı	pF
C _{rss}	Reverse Transfer Capacitance			-	1260	ı	pF
R_{G}	Gate Resistance	$V_{GS} = 0.5V, f = 1I$	MHz	•	1.2	ı	Ω
$Q_{g(TOT)}$	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V		•	204	265	nC
$Q_{g(5)}$	Total Gate Charge at 5V	$V_{GS} = 0 \text{ to } 5V$		•	100	130	nC
$Q_{g(TH)}$	Threshold Gate Charge	$V_{GS} = 0$ to 1V	$V_{DD} = 15V$ $I_{D} = 80A$	•	10.9	14.2	nC
Q_{gs}	Gate to Source Gate Charge		$I_0 = 60A$ $I_0 = 1.0mA$	•	33	ı	nC
Q _{gs2}	Gate Charge Threshold to Plateau		.g	-	22		nC
Q_{gd}	Gate to Drain "Miller" Charge			-	43	-	nC

Electrical Characteristics $T_J = 25^{\circ}C$ unless otherwise noted

Symbo	I Parameter	Test Conditions	Min	Тур	Max	Units
Switch	ing Characteristics					
t _(on)	Turn-On Time		-	-	155	ns
t _{d(on)}	Turn-On Delay Time		-	24	-	ns
t _r	Turn-On Rise Time	$V_{DD} = 15V, I_{D} = 80A$ $V_{GS} = 5V, R_{GS} = 1.5\Omega$	-	73	-	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 5V$, $R_{GS} = 1.5\Omega$	-	54	-	ns
t _f	Turn-Off Fall Time		-	38	-	ns
t _{off}	Turn-Off Time		-	-	149	ns

Drain-Source Diode Characteristics

V	Source to Drain Diode Voltage	I _{SD} = 75A	-	0.8	1.25	V
V _{SD} So	Source to Drain Diode Voltage	I _{SD} = 40A	-	0.8	1.0	٧
t _{rr}	Reverse Recovery Time	$I_F = 75A$, di/dt = 100A/ μ s	-	59	77	ns
Q _{rr}	Reverse Recovery Charge	$I_F = 75A$, di/dt = 100A/ μ s	-	67	87	nC

Notes: 1: Starting $T_J = 25^{\circ}C$, L = 0.61 mH, $I_{AS} = 64 A$, $V_{DD} = 30 V$, $V_{GS} = 10 V$. 2: Pulse width = 100s.

This product has been designed to meet the extreme test conditions and environment demanded by the automotive industry. For a copy of the requirements, see AEC Q101 at: http://www.aecouncil.com/
All Fairchild Semiconductor products are manufactured, assembled and tested under ISO9000 and QS9000 quality systems certification.

Typical Characteristics 350 POWER DISSIPATION MULIPLIER 7.0 9.0 0.1 7.1 10 8.0 0.1 **CURRENT LIMITED** 300 BY PACKAGE ID, DRAIN CURRENT (A) 250 V_{GS} = 10V 200 150 100 50 0.0 0 25 50 75 100 125 150 175 50 175 25 75 100 125 150 T_C, CASE TEMPERATURE(°C) T_C, CASE TEMPERATURE(°C)

Figure 1. Normalized Power Dissipation vs Case Temperature

Figure 2. Maximum Continuous Drain Current vs Case Temperature

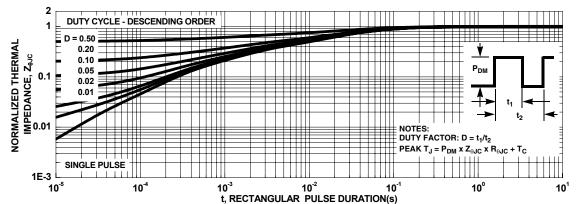


Figure 3. Normalized Maximum Transient Thermal Impedance

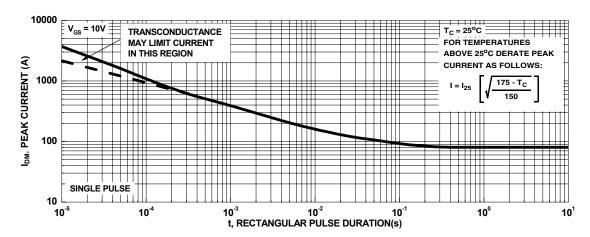


Figure 4. Peak Current Capability

Typical Characteristics

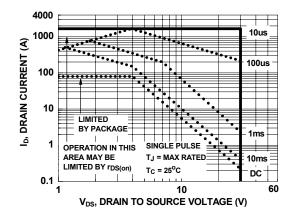
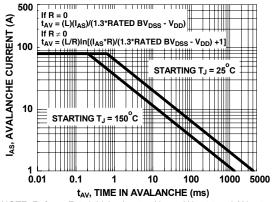


Figure 5. Forward Bias Safe Operating Area



NOTE: Refer to Fairchild Application Notes AN7514 and AN7515

Figure 6. Unclamped Inductive Switching Capability

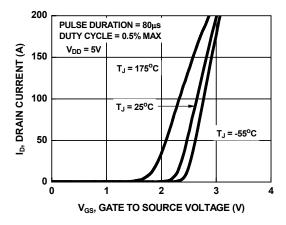


Figure 7. Transfer Characteristics

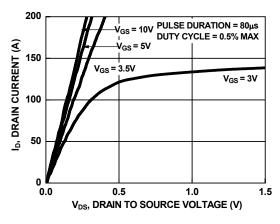


Figure 8. Saturation Characteristics

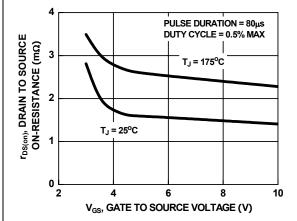


Figure 9. Drain to Source On-Resistance Variation vs Gate to Source Voltage

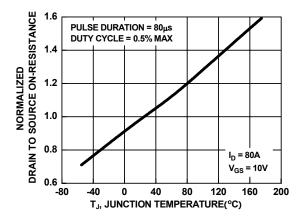


Figure 10. Normalized Drain to Source On Resistance vs Junction Temperature

Typical Characteristics

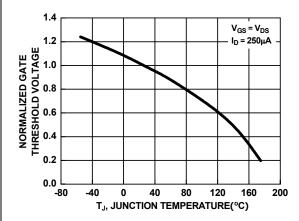


Figure 11. Normalized Gate Threshold Voltage vs
Junction Temperature

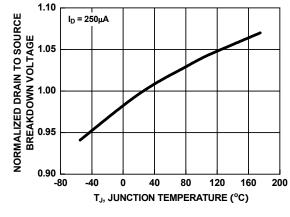


Figure 12. Normalized Drain to Source Breakdown Voltage vs Junction Temperature

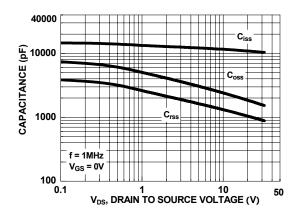


Figure 13. Capacitance vs Drain to Source Voltage

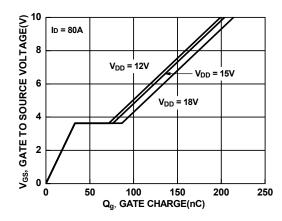


Figure 14. Gate Charge vs Gate to Source Voltage





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